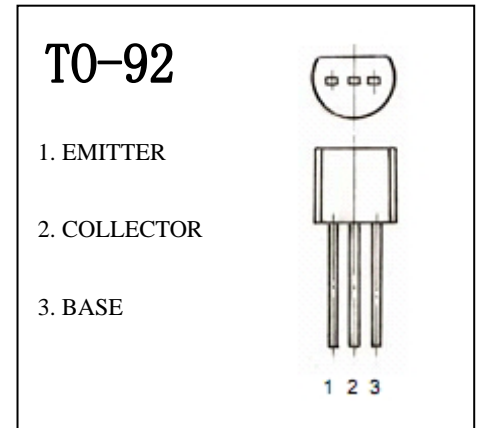




D965 TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	42	V
VCEO	Collector-Emitter Voltage	22	V
VEBO	Emitter-Base Voltage	6	V
IC	Collector Current	5.0	A
PC	Collector Power Dissipation	750	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	42			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	22			V
Emitter-base breakdown voltage	V(BR)EBO	IC=100uA, IC=0	6			V
Collector cut-off current	ICBO	VCB=42V, IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB=6V, IC=0			0.1	μA
DC current gain	HFE	Vce=2V, Ic=500mA	500		1500	
Collector-emitter saturation voltage	VCE(sat)	IC=3000mA, IB=100mA			0.35	V
Transition frequency	fT	VCE=6V, IC=50mA, f=30MHZ		150		MHz